**Product data sheet** 

# 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

#### 2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	12.5	А
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 45 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	1	А
Static characte	eristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	0.2	-	3	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{\text{Fig. 7}}$	0.2	-	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	0.2	-	5	mA

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate	<u>                                     </u>	Sym051
3	T1	main terminal 1	3 2 1 TO-92 (SOT54)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
Z0103NA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 45 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	1	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	12.5	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	13.8	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 1 \text{ A}$ ; $I_G = 20 \text{ mA}$ ; $dI_G/dt = 100 \text{ mA}/$ $\mu$ s; $T2+ G+$	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/ $\mu$ s; T2+ G-	-	50	A/µs
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Symbol	Parameter	Conditions	Min	Max	Unit
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/ $\mu$ s; T2- G-	-	50	A/µs
		$I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/ $\mu$ s; T2- G+	-	20	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

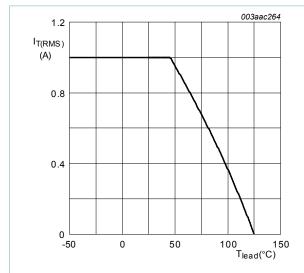
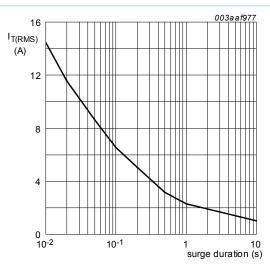
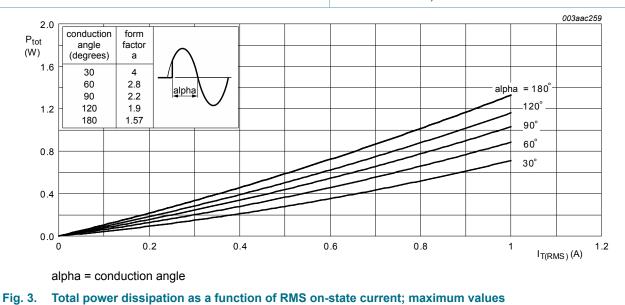


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz;  $T_{lead} = 45 \,^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values



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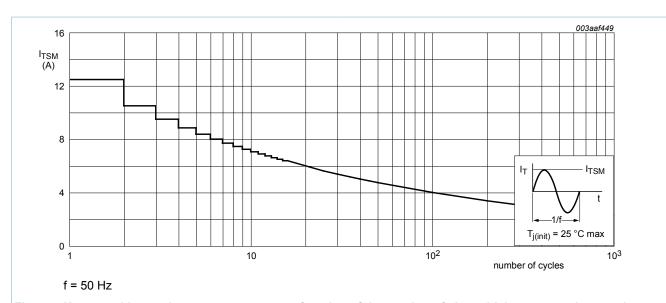
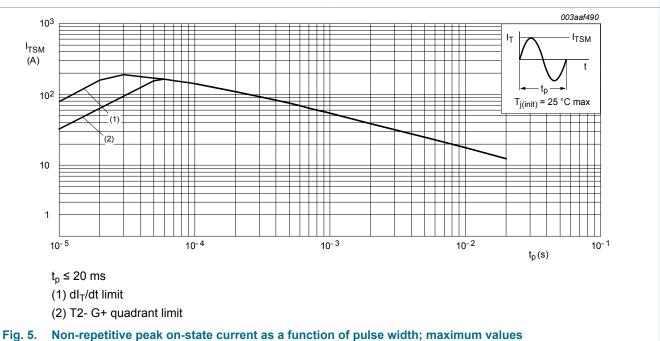


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



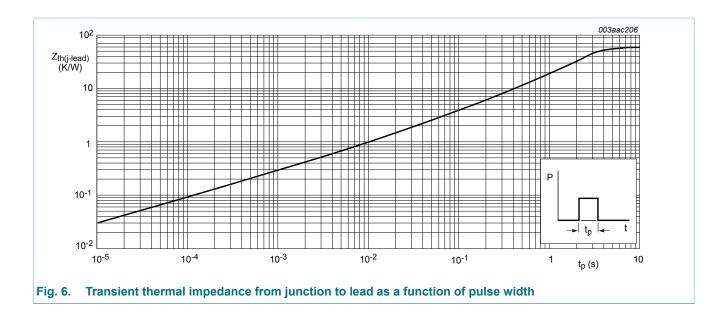
### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	full cycle; printed circuit board mounted; lead length 4 mm	-	150	-	K/W

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## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	0.2	-	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	0.2	-	5	mA
I <u>L</u>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	7	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	7	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	7	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	-	1	V

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		V <sub>D</sub> = 800 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11		0.2	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C		-	-	0.5	mA
Dynamic ch	naracteristics		1	1	'		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12		80	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 110 °C; $dI_{com}$ / dt = 0.44 A/ms; gate open circuit		0.5	-	-	V/µs

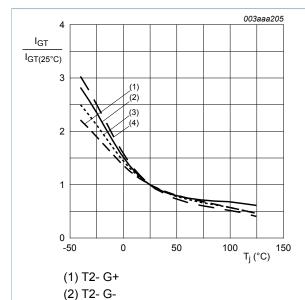


Fig. 7. Normalized gate trigger current as a function of junction temperature

(3) T2+ G-(4) T2+ G+

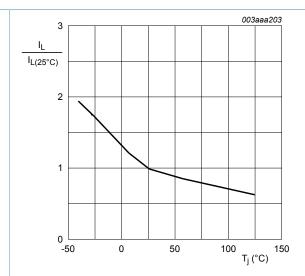


Fig. 8. Normalized latching current as a function of junction temperature

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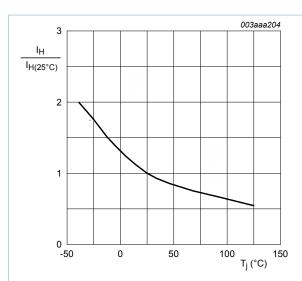
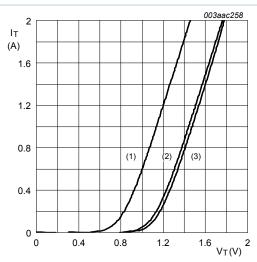


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.13 \text{ V}$ 

 $R_s = 0.31 \Omega$ 

(1)  $T_j$  = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

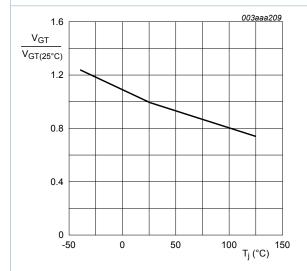
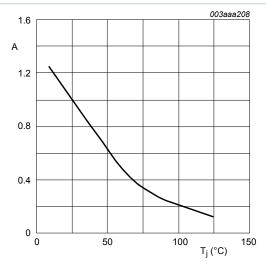


Fig. 11. Normalized gate trigger voltage as a function of Fig. 12. Normalized critical rate of rise of off-state junction temperature



voltage as a function of junction temperature; typical values

$$A = \frac{d\mathrm{V}_{D(Tj\,\circ\,C)}\,/\,\,dt}{d\mathrm{V}_{D(25\,\circ\,C)}\,/\,\,dt}$$

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# 10. Package outline

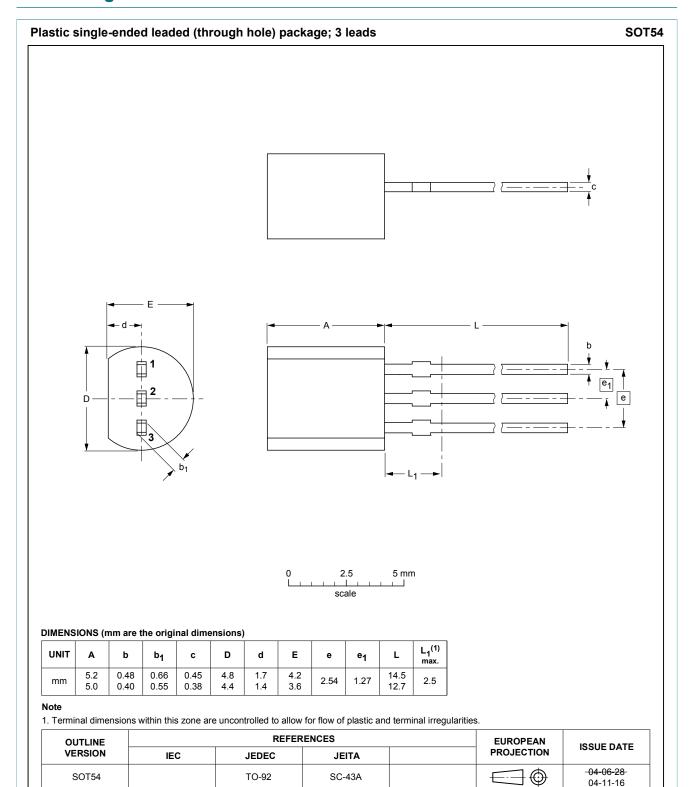


Fig. 13. Package outline TO-92 (SOT54)

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